

LED760-40K32 stem type LED with high beam

LED760-40K32 is AlGaAs LED mounted on TO-46 stem with ball glass lens, being designed for high beam uses.

On forward bias it emits a spectral band of radiation, which peaks at 760 nm.

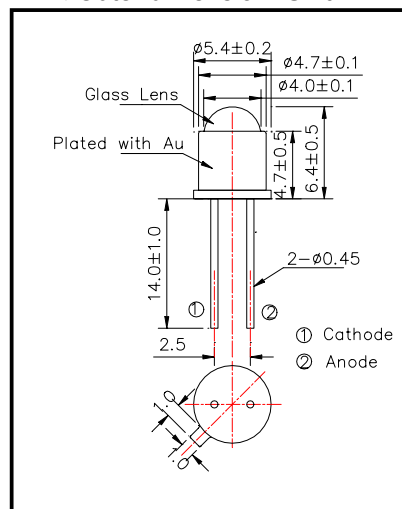
◆Outer dimension •Unit:mm•

◆Features

- High radiated intensity
- High Reliability

◆Specifications

- Product Name Infrared LED Lamp
- Type No. LED760-40K32
- Chip Spec.
- Material AlGaAs
- Peak Wavelength 760 nm
- Package TO-46 stem
- Type Ball glass lens
- Lens Gold plated



◆Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	200	mW	T _a = 25° C
Forward Current	I _F	100	mA	T _a = 25° C
Pulse Forward Current	I _{FP}	500	mA	T _a = 25° C
Reverse Voltage	V _R	5	V	T _a = 25° C
Operating Temperature	T _{OPR}	-30 ~ +80	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	260	°C	

‡Pulse Forward Current condition: Duty = 1% and Pulse Width=10 μs.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 260° C

◆Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F = 50 mA		1.85	2.00	V
Reverse Current	I _R	V _R = 5V			10	uA
Total Radiated Power	P _O	I _F = 50 mA	6	10		mW
Radiant Intensity	I _E	I _F = 50 mA		50.0		mW/sr
Peak Wavelength	λ _P	I _F = 50 mA	740	760	780	nm
Half Width	Δλ	I _F = 50 mA		30		nm
Viewing Half Angle	θ _{1/2}	I _F = 50 mA		±10		deg.
Rise Time	••	I _F = 50 mA		80		ns
Fall Time	••	I _F = 50 mA		80		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.

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